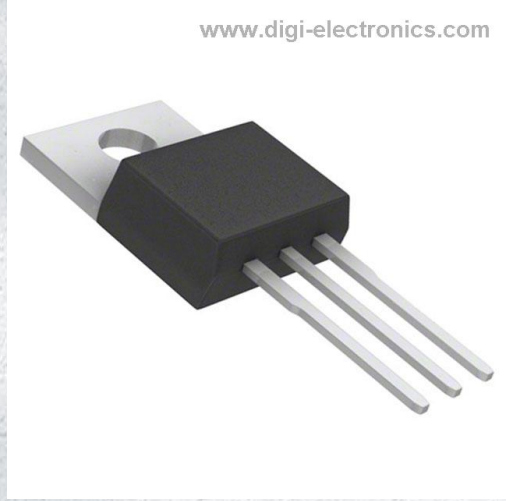
FQP9N25C Datasheet



DiGi Electronics Part Number	FQP9N25C-DG
Manufacturer	onsemi
Manufacturer Product Number	FQP9N25C
Description	MOSFET N-CH 250V 8.8A TO220-3
Detailed Description	N-Channel 250 V 8.8A (Tc) 74W (Tc) Through Hole TO-220-3

https://www.DiGi-Electronics.com

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
FQP9N25C	onsemi
Series:	Product Status:
QFET®	Obsolete
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
250 V	8.8A (Tc)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
10V	430mOhm @ 4.4A, 10V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
4V @ 250µA	35 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±30V	710 pF @ 25 V
FET Feature:	Power Dissipation (Max):
-	74W (Tc)
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Through Hole
Supplier Device Package:	Package / Case:
TO-220-3	TO-220-3
Base Product Number:	
FQP9	

Environmental & Export classification

Moisture Sensitivity Level (MSL):	REACH Status:
1 (Unlimited)	REACH Unaffected
ECCN:	HTSUS:
EAR99	8541.29.0095

FAIRCHILD SEMICONDUCTOR®

March 2013

FQP9N25C / FQPF9N25C

N-Channel QFET® MOSFET

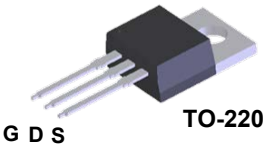
250 V, 8.8 A, 430 mΩ

Description

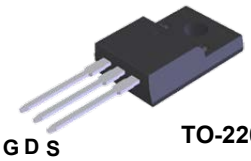
This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor®'s proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

Features

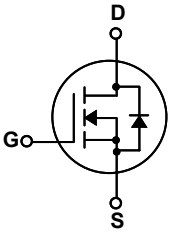
- 8.8 A, 250 V, $R_{DS(on)}$=430 mΩ(Max.)@V_{GS}=10 V, I_D=4.4 A
- Low Gate Charge (Typ. 26.5 nC)
- Low C_{rss} (Typ. 45.5 pF)
- 100% Avalanche Tested



TO-220



TO-220F



Absolute Maximum Ratings

T_C = 25°C unless otherwise noted

Symbol	Parameter		FQP9N25C	FQPF9N25C	Unit
V_{DSS}	Drain-Source Voltage		250		V
I_D	Drain Current - Continuous (T_C = 25°C)		8.8	8.8 *	A
	- Continuous (T_C = 100°C)		5.6	5.6 *	A
I_{DM}	Drain Current - Pulsed	(Note 1)	35.2	35.2 *	A
V_{GSS}	Gate-Source Voltage		± 30		V
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	285		mJ
I_{AR}	Avalanche Current	(Note 1)	8.8		A
E_{AR}	Repetitive Avalanche Energy	(Note 1)	7.4		mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	5.5		V/ns
P_D	Power Dissipation (T_C = 25°C)		74	38	W
	- Derate above 25°C		0.59	0.3	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150		°C
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300		°C

* Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	FQP9N25C	FQPF9N25C	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	1.69	3.29	°C/W
$R_{\theta JS}$	Thermal Resistance, Case-to-Sink Typ.	0.5	--	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	62.5	°C/W

Electrical Characteristics

T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 μA	250	--	--	V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C	--	0.30	--	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 250 V, V_{GS} = 0 V	--	--	10	μA
		V_{DS} = 200 V, T_C = 125°C	--	--	100	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = 30 V, V_{DS} = 0 V	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -30 V, V_{DS} = 0 V	--	--	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 μA	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = 10 V, I_D = 4.4 A	--	0.35	0.43	Ω
g_{FS}	Forward Transconductance	V_{DS} = 40 V, I_D = 4.4 A (Note 4)	--	7.0	--	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25 V, V_{GS} = 0 V, f = 1.0 MHz	--	545	710	pF
C_{oss}	Output Capacitance		--	115	150	pF
C_{rss}	Reverse Transfer Capacitance		--	45.5	60	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 125 V, I_D = 8.8 A, R_G = 25 Ω (Note 4, 5)	--	15	40	ns
t_r	Turn-On Rise Time		--	85	180	ns
$t_{d(off)}$	Turn-Off Delay Time		--	90	190	ns
t_f	Turn-Off Fall Time		--	65	140	ns
Q_g	Total Gate Charge	V_{DS} = 200 V, I_D = 8.8 A, V_{GS} = 10 V (Note 4, 5)	--	26.5	35	nC
Q_{gs}	Gate-Source Charge		--	3.5	--	nC
Q_{gd}	Gate-Drain Charge		--	13.5	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	8.8	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	35.2	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 8.8 A	--	--	1.5	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_S = 8.8 A, dI_F / dt = 100 A/μs (Note 4)	--	218	--	ns
Q_{rr}	Reverse Recovery Charge		--	1.58	--	μC

Notes:
1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L = 5.9mH, I_{AS} = 8.8A, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25°C
3. I_{SD} ≤ 8.8A, di/dt ≤ 300A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%
5. Essentially independent of operating temperature

Typical Characteristics

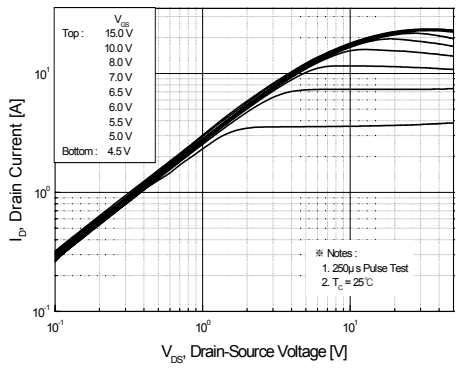


Figure 1. On-Region Characteristics

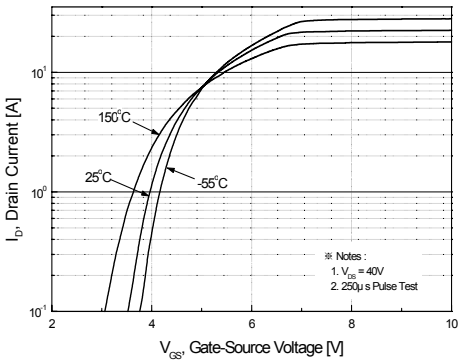


Figure 2. Transfer Characteristics

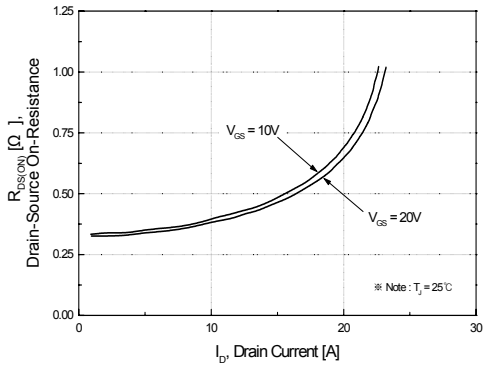


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

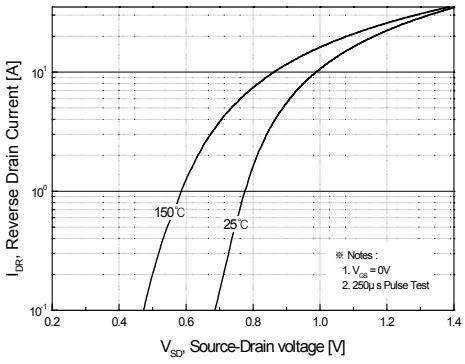


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

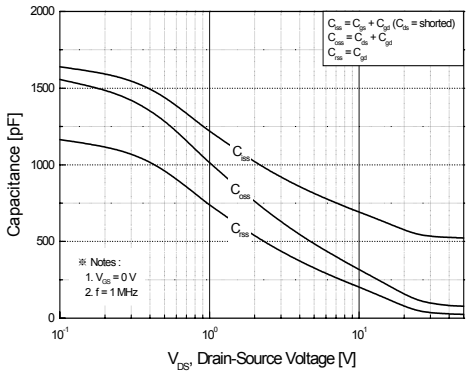


Figure 5. Capacitance Characteristics

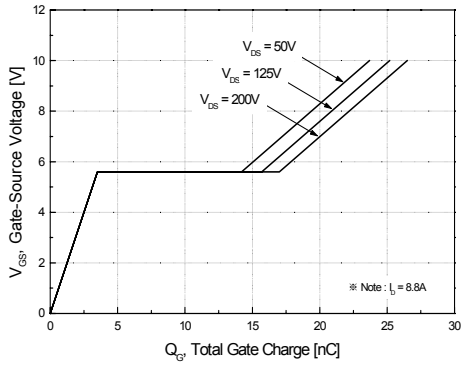


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

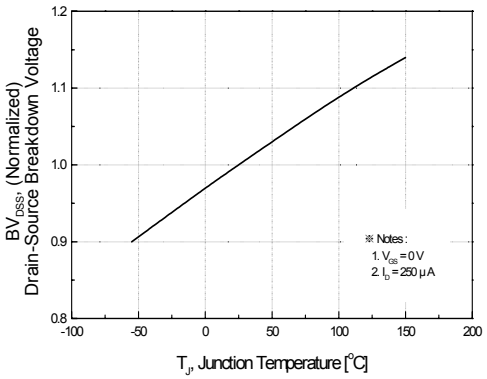


Figure 7. Breakdown Voltage Variation vs Temperature

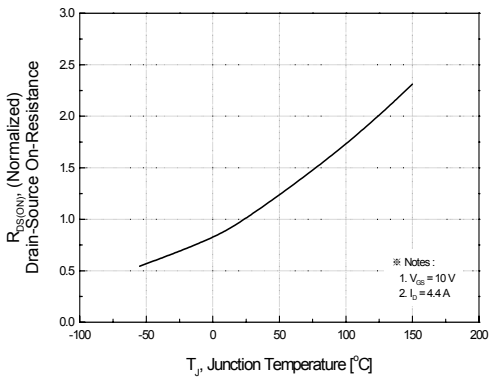


Figure 8. On-Resistance Variation vs Temperature

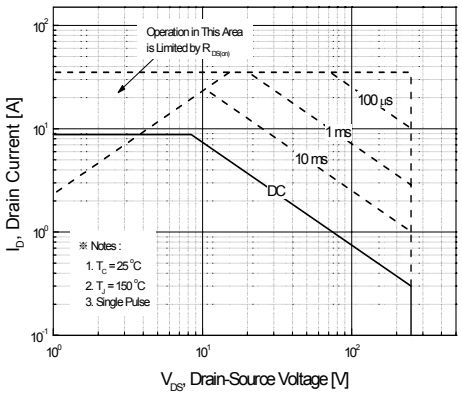


Figure 9-1. Maximum Safe Operating Area for FQP9N25C

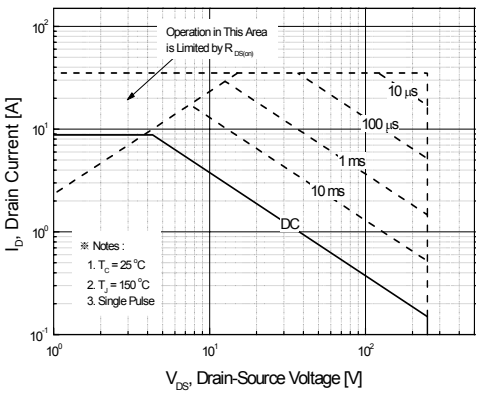


Figure 9-2. Maximum Safe Operating Area for FQPF9N25C

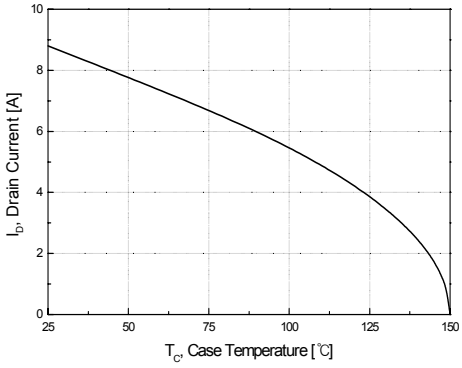


Figure 10. Maximum Drain Current vs Case Temperature

Typical Characteristics (Continued)

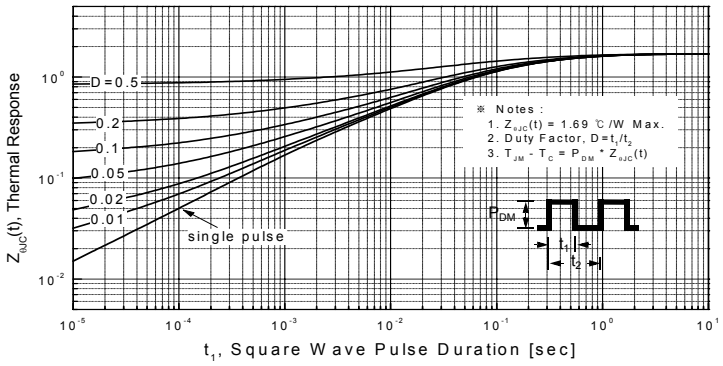


Figure 11-1. Transient Thermal Response Curve for FQP9N25C

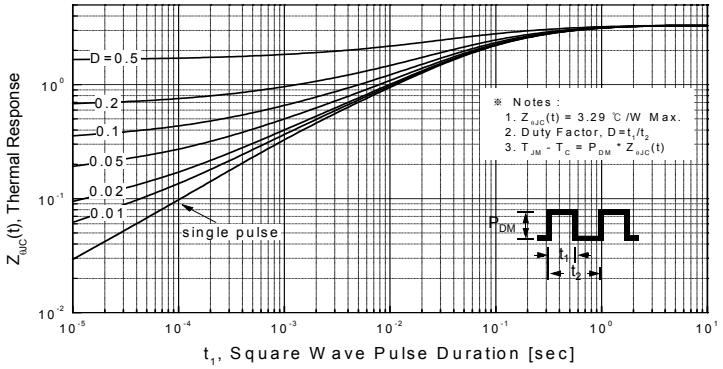
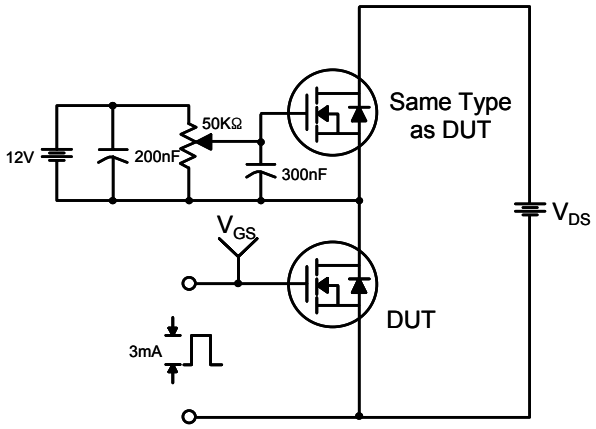
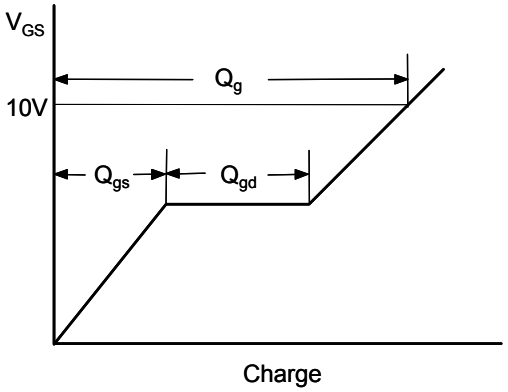


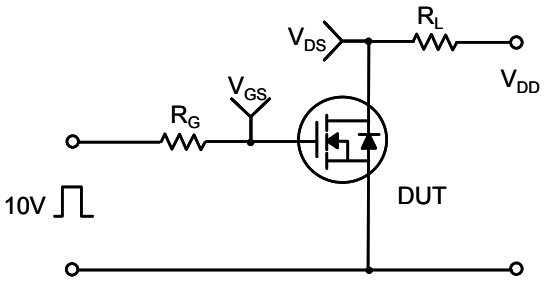
Figure 11-2. Transient Thermal Response Curve for FQPF9N25C

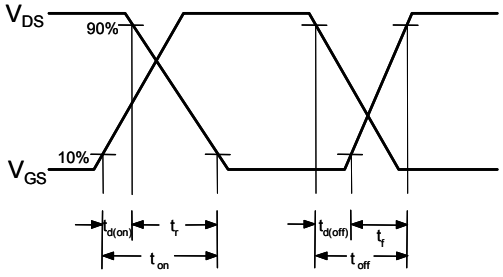
Gate Charge Test Circuit & Waveform



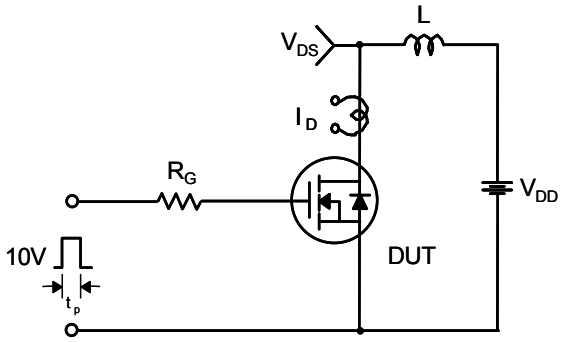


Resistive Switching Test Circuit & Waveforms

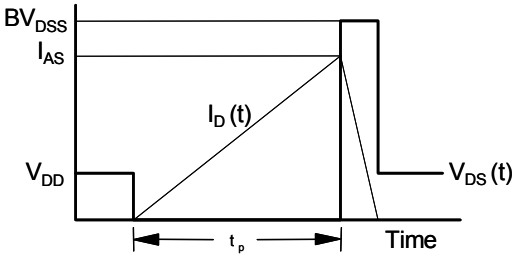




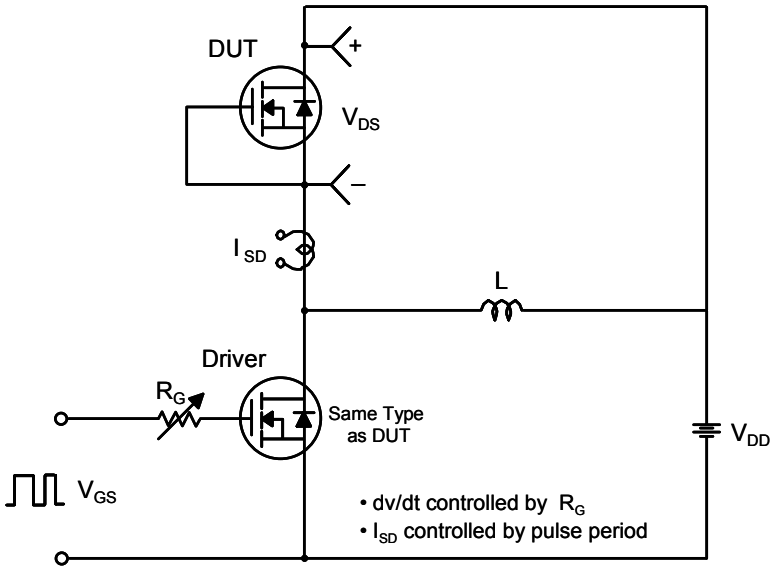
Unclamped Inductive Switching Test Circuit & Waveforms

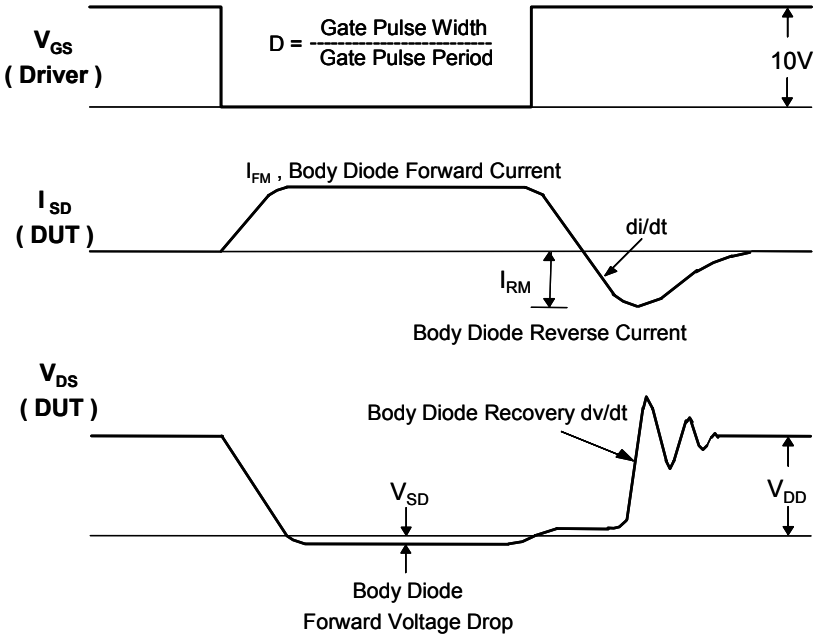


$$E_{AS} = \frac{1}{2} L I_{AS}^2 \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$



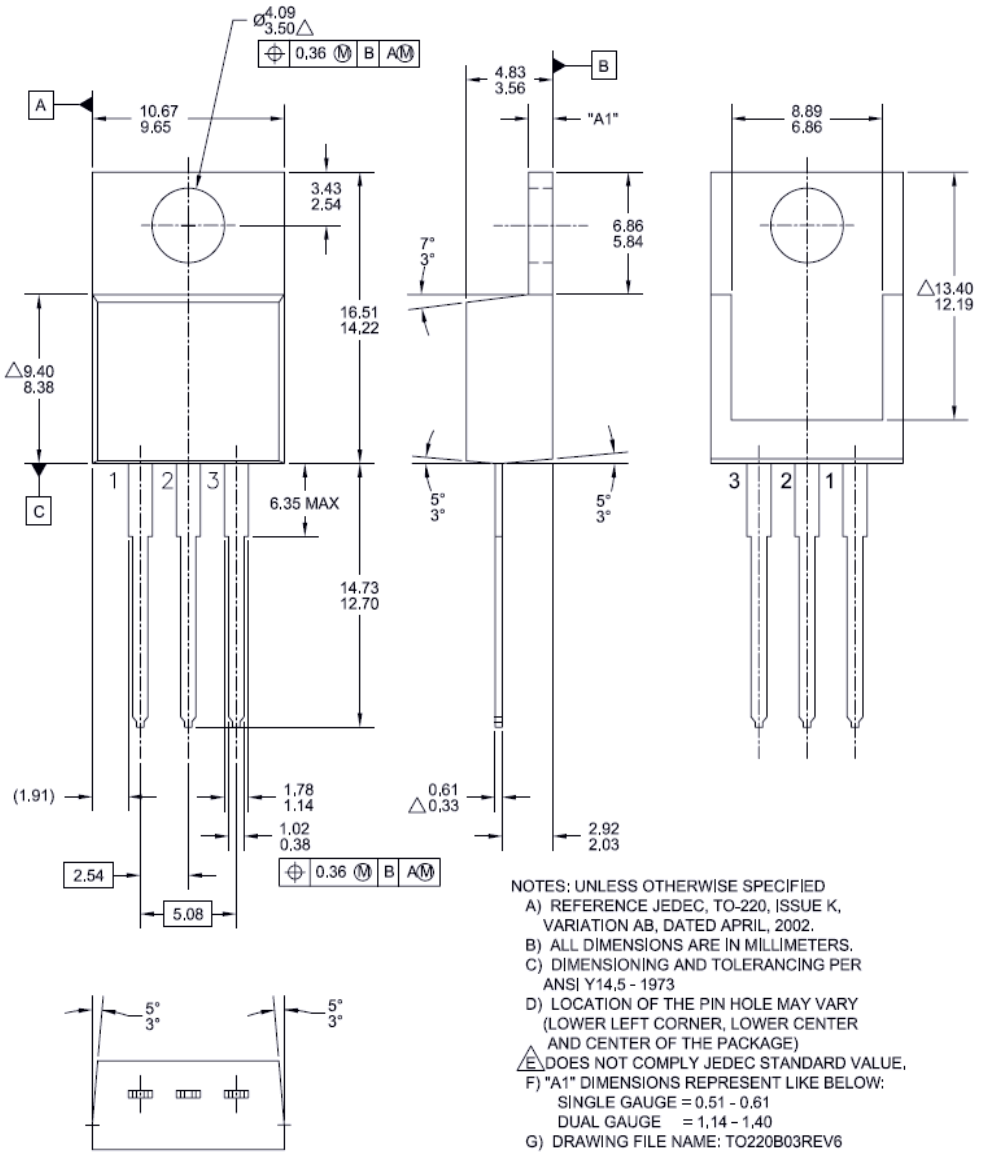
Peak Diode Recovery dv/dt Test Circuit & Waveforms





Mechanical Dimensions

TO-220

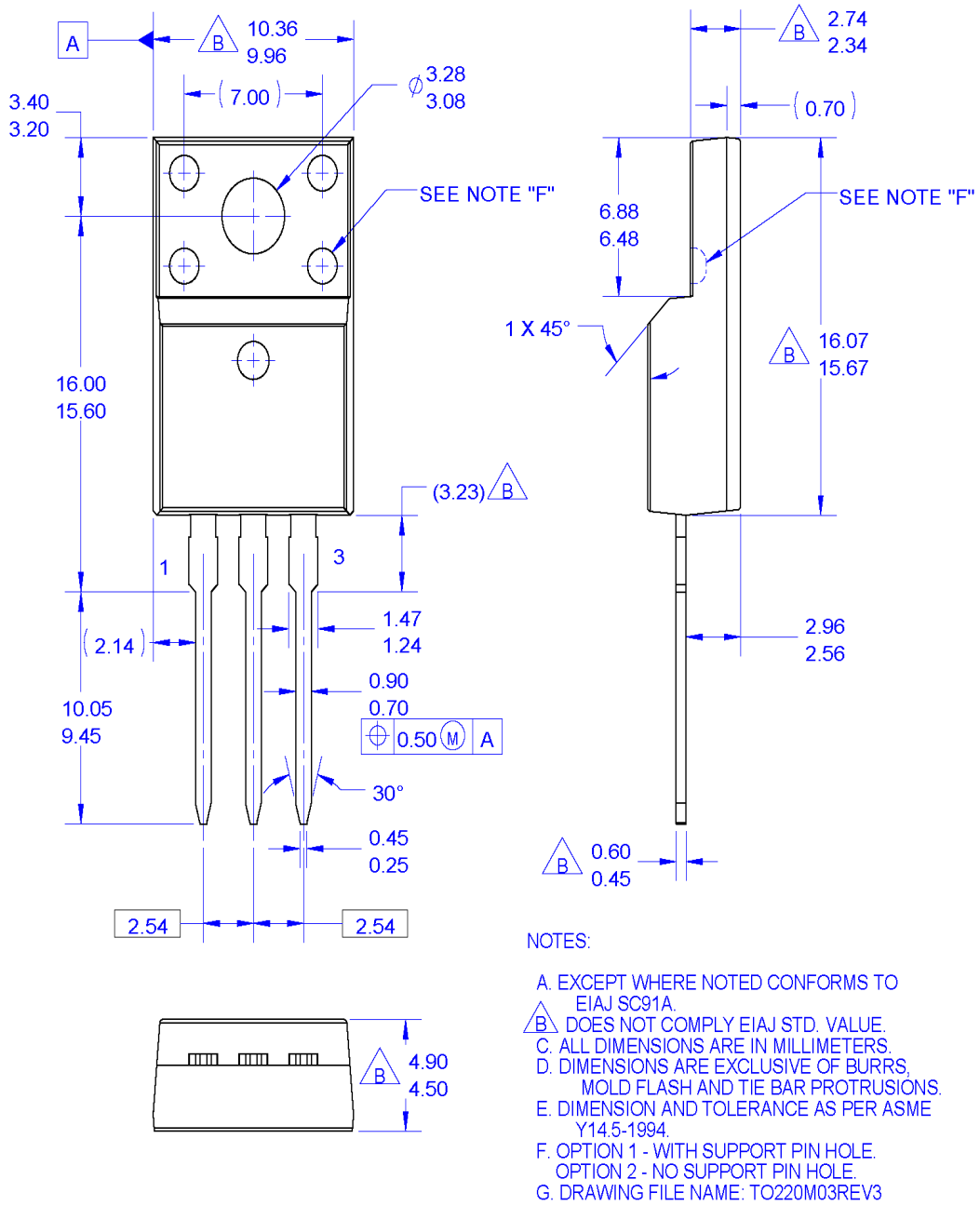


NOTES: UNLESS OTHERWISE SPECIFIED
A) REFERENCE JEDEC, TO-220, ISSUE K, VARIATION AB, DATED APRIL, 2002.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONING AND TOLERANCING PER ANSI Y14,5 - 1973
D) LOCATION OF THE PIN HOLE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE)
△E DOES NOT COMPLY JEDEC STANDARD VALUE,
F) "A1" DIMENSIONS REPRESENT LIKE BELOW:
SINGLE GAUGE = 0.51 - 0.61
DUAL GAUGE = 1,14 - 1,40
G) DRAWING FILE NAME: TO220B03REV6

Dimensions in Millimeters

Mechanical Dimensions

TO-220F



NOTES:

A. EXCEPT WHERE NOTED CONFORMS TO EIAJ SC91A.
B. DOES NOT COMPLY EIAJ STD. VALUE.
C. ALL DIMENSIONS ARE IN MILLIMETERS.
D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
E. DIMENSION AND TOLERANCE AS PER ASME Y14.5-1994.
F. OPTION 1 - WITH SUPPORT PIN HOLE.
OPTION 2 - NO SUPPORT PIN HOLE.
G. DRAWING FILE NAME: TO220M03REV3

Dimensions in Millimeters

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2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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PRODUCT STATUS DEFINITIONS
Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. I64

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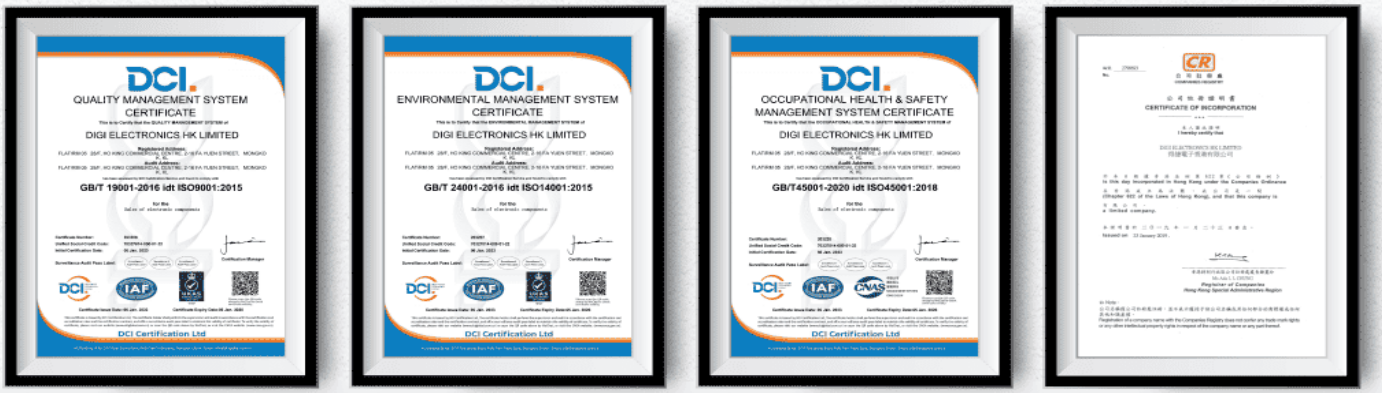

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